



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Sheu, et al.

Docket No.:

TSM03-0140

Serial No.:

10/619,828

Art Unit:

2814

Filed:

July 15, 2003

Examiner:

Dana Farahani

For:

Self-Aligned MOSFET having an Oxide Region below the Channel

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Respectfully submitted,

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The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & 08B that may be considered material to the examination of the above-identified application.

This Information Disclosure Statement is submitted under 37 C.F.R. §1.97(b) as no Office Action on the merits has been received. If any fee is required, please charge any additional amount, or credit any overpayment to Deposit Acct. No 50-1065 of the below mentioned firm.

Respectfully submitted,

May 26, 2004

Date

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PTO/SB/08A (02-03)
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Complete if Known	
Application Number	10/619,828
Filing Date	July 15, 2003
First Named Inventor	Sheu, et al.
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Examiner Name	Farahani
Attorney Docket Number	TSM03-0140

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No.1	Document Number Number - Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
	1	US-4,314,269	02-02-1982	Fujiki	
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Examiner Initials*	Cite No.1	Foreign Patent Document Country Code ³ - Number ⁴ - Kind Code ⁵ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶
	21	WO 03/017336 A2	02-27-2003	Amberwave Systems Corporation		
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Examiner	Date	
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Sheet

Complete if Known Application Number 10/619,828 Filing Date July 15, 2003 First Named Inventor Sheu, et al. Group Art Unit 2814 **Examiner Name** Farahani Attorney Docket Number TSM03-0140

	т—	OTHER PRIOR ART NON PATENT LITERATURE DOCUMENTS	_
Examiner Initials*	Cite ₁ No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	
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